

# ZXTP19020DZ

## 20V PNP high gain transistor in SOT89

### Summary

$BV_{CEO} > -20V$

$BV_{ECO} > -4V$

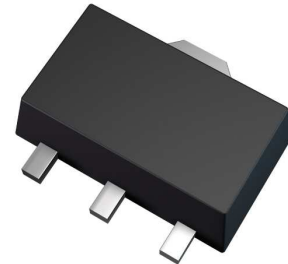
$I_{C(cont)} = 6A$

$V_{CE(sat)} < -47mV @ -1A$

$R_{CE(sat)} = 28m\Omega$

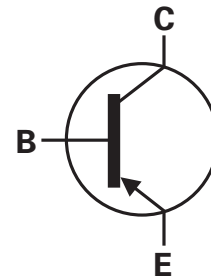
$P_D = 2.4W$

Complementary part number ZXTN19020DZ



### Description

Packaged in the SOT89 outline this new low saturation PNP transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions.

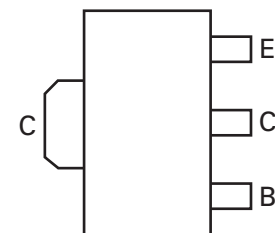


### Features

- Higher power dissipation SOT89 package
- High gain
- High peak current
- Low saturation voltages
- 4V reverse blocking voltage

### Applications

- Power disconnect switch
- Battery chargers
- High side drivers
- Motor drive



Pinout - top view

### Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP19020DZTA	7	12	1000

### Device marking

1M1

## Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-Base voltage	$V_{CBO}$	-25	V
Collector-Emitter voltage	$V_{CEO}$	-20	V
Emitter-Collector voltage (reverse blocking)	$V_{ECO}$	-4	V
Emitter-Base voltage	$V_{EBO}$	-7	V
Continuous Collector current <sup>(c)</sup>	$I_C$	-6	A
Base current	$I_B$	-1	A
Peak pulse current	$I_{CM}$	-15	A
Power dissipation at $T_A = 25^\circ\text{C}^{(a)}$	$P_D$	1.1	W
Linear derating factor		8.8	mW/°C
Power dissipation at $T_A = 25^\circ\text{C}^{(b)}$	$P_D$	1.8	W
Linear derating factor		14.4	mW/°C
Power dissipation at $T_A = 25^\circ\text{C}^{(c)}$	$P_D$	2.4	W
Linear derating factor		19.2	mW/°C
Power dissipation at $T_A = 25^\circ\text{C}^{(d)}$	$P_D$	4.46	W
Linear derating factor		35.7	mW/°C
Power dissipation at $T_C = 25^\circ\text{C}^{(e)}$	$P_D$	26.7	W
Linear derating factor		213	mW/°C
Operating and storage temperature range	$T_j, T_{stg}$	-55 to 150	°C

## Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient <sup>(a)</sup>	$R_{\theta JA}$	117	°C/W
Junction to ambient <sup>(b)</sup>	$R_{\theta JA}$	68	°C/W
Junction to ambient <sup>(c)</sup>	$R_{\theta JA}$	51	°C/W
Junction to ambient <sup>(d)</sup>	$R_{\theta JA}$	117	°C/W
Junction to case <sup>(e)</sup>	$R_{\theta JC}$	4.69	°C/W

### NOTES:

(a) For a device surface mounted on 15mm x 15mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

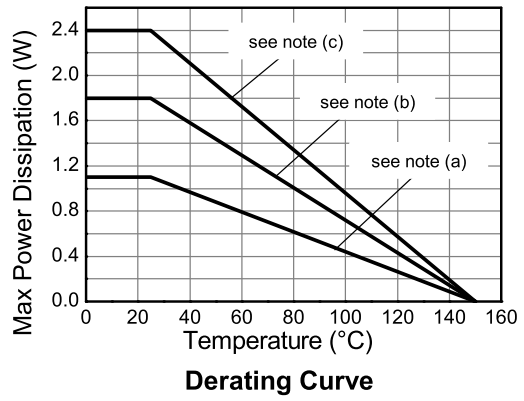
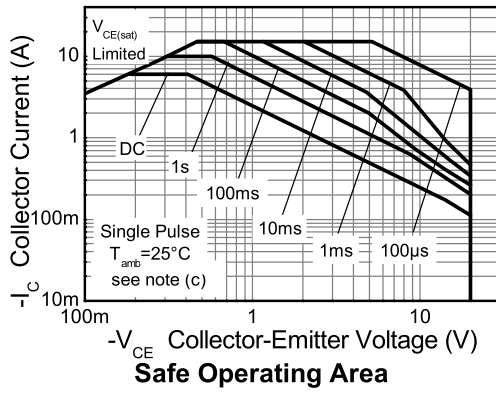
(b) Mounted on 25mm x 25mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(c) Mounted on 50mm x 50mm x 0.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.

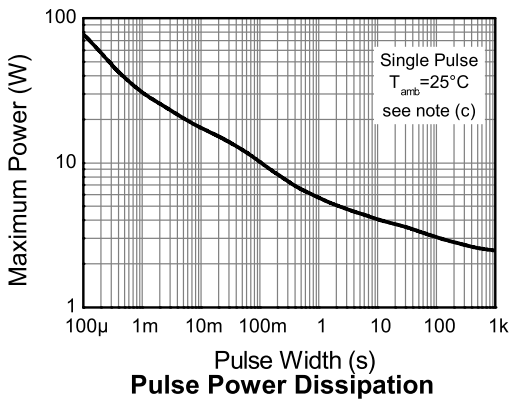
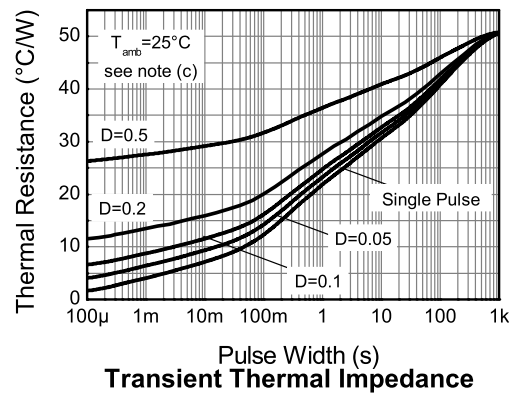
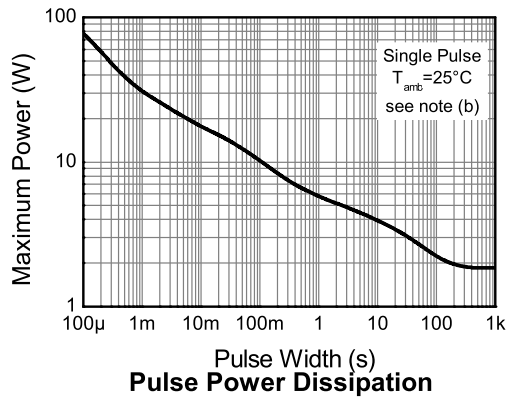
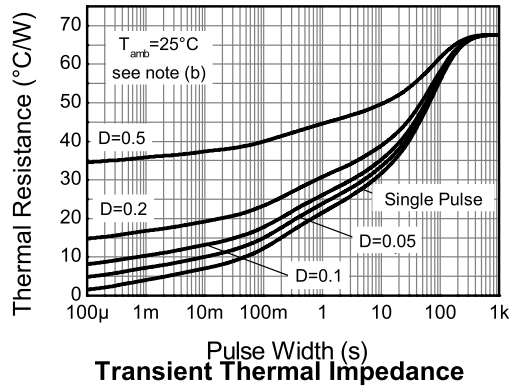
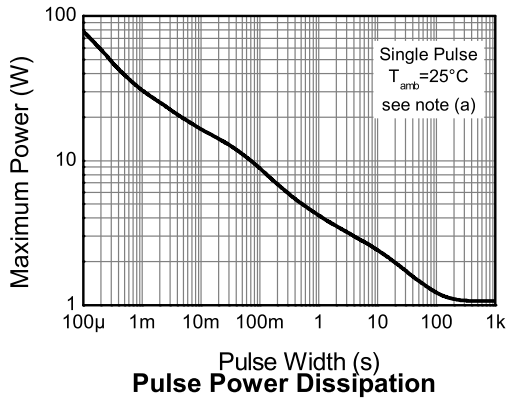
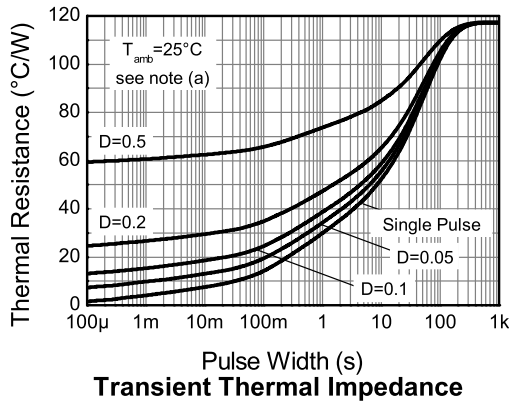
(d) As (c) above measured at  $t < 5$  seconds.

(e) Junction to case (collector tab). Typical

## Thermal characteristics



## Thermal characteristics



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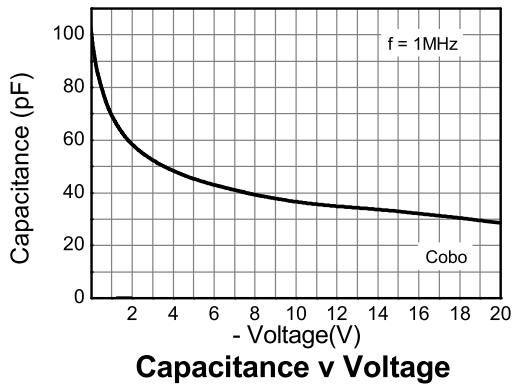
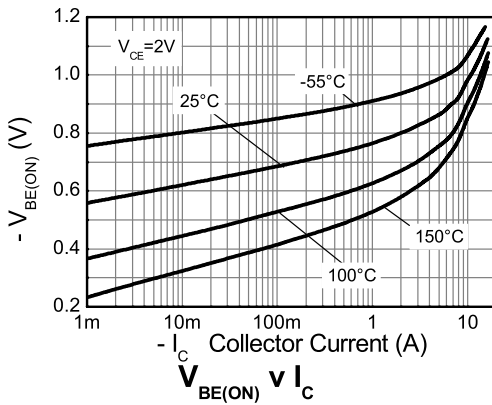
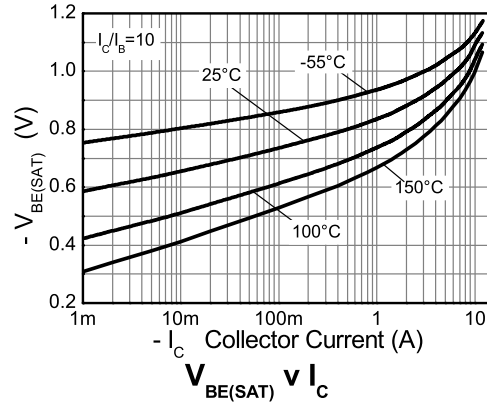
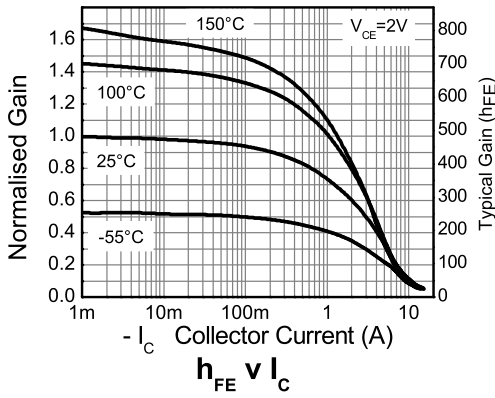
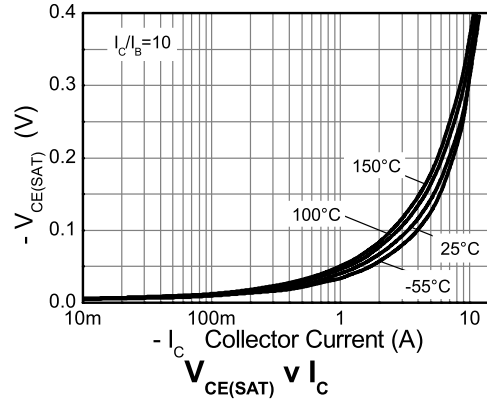
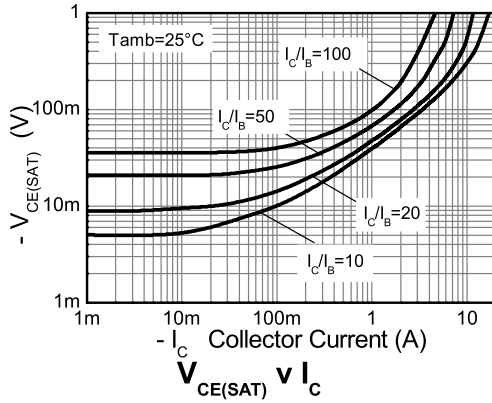
## Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-Base breakdown voltage	$BV_{CBO}$	-25	-55		V	$I_C = -100\mu\text{A}$
Collector-Emitter breakdown voltage	$BV_{CEO}$	-20	-50		V	$I_C = -10\text{mA}^{(*)}$
Emitter-Collector breakdown voltage (reverse blocking)	$BV_{ECX}$	-4	-8.6		V	$I_E = -100\mu\text{A}$ , $R_{BC} < 1\text{k}\Omega$ or $0.25\text{V} > V_{BC} > -0.25\text{V}$
Emitter-Collector breakdown voltage (reverse blocking)	$BV_{ECO}$	-4	-8.6		V	$I_E = -100\mu\text{A}$
Emitter-Base breakdown voltage	$BV_{EBO}$	-7	-8.2		V	$I_E = -100\mu\text{A}$
Collector-Base cut-off current	$I_{CBO}$		<1	50 0.5	nA $\mu\text{A}$	$V_{CB} = -25\text{V}$ $V_{CB} = -25\text{V}$ , $T_{amb} = 100^{\circ}\text{C}$
Emitter cut-off current	$I_{EBO}$		<1	-50	nA	$V_{EB} = -5.6\text{V}$
Collector-Emitter saturation voltage	$V_{CE(sat)}$		-40 -100 -115 -225	-47 -130 -145 -275	mV mV mV mV	$I_C = -1\text{A}$ , $I_B = -100\text{mA}^{(*)}$ $I_C = -1\text{A}$ , $I_B = -10\text{mA}^{(*)}$ $I_C = -2\text{A}$ , $I_B = -40\text{mA}^{(*)}$ $I_C = -6\text{A}$ , $I_B = -300\text{mA}^{(*)}$
Base-Emitter saturation voltage	$V_{BE(sat)}$		-1000	-1100	mV	$I_C = -6\text{A}$ , $I_B = -300\text{mA}^{(*)}$
Base-Emitter turn-on voltage	$V_{BE(on)}$		-865	-1000	mV	$I_C = -6\text{A}$ , $V_{CE} = -2\text{V}^{(*)}$
Static forward current transfer ratio	$h_{FE}$	300 200 65	450 290 110 25	900		$I_C = -100\text{mA}$ , $V_{CE} = -2\text{V}^{(*)}$ $I_C = -2\text{A}$ , $V_{CE} = -2\text{V}^{(*)}$ $I_C = -6\text{A}$ , $V_{CE} = -2\text{V}^{(*)}$ $I_C = -15\text{A}$ , $V_{CE} = -2\text{V}^{(*)}$
Transition frequency	$f_T$		176		MHz	$I_C = -50\text{mA}$ , $V_{CE} = -10\text{V}$ $f = 50\text{MHz}$
Input capacitance	$C_{ibo}$			400	pF	$V_{EB} = -0.5\text{V}$ , $f = 1\text{MHz}^{(*)}$
Output capacitance	$C_{obo}$		36	45	pF	$V_{CB} = -10\text{V}$ , $f = 1\text{MHz}^{(*)}$
Delay time	$t_d$		23		ns	$I_C = -1\text{A}$ , $V_{CC} = -10\text{V}$ , $I_{B1} = -I_{B2} = -50\text{mA}$
Rise time	$t_r$		18.4		ns	
Storage time	$t_s$		266		ns	
Fall time	$t_f$		49.6		ns	

### NOTES:

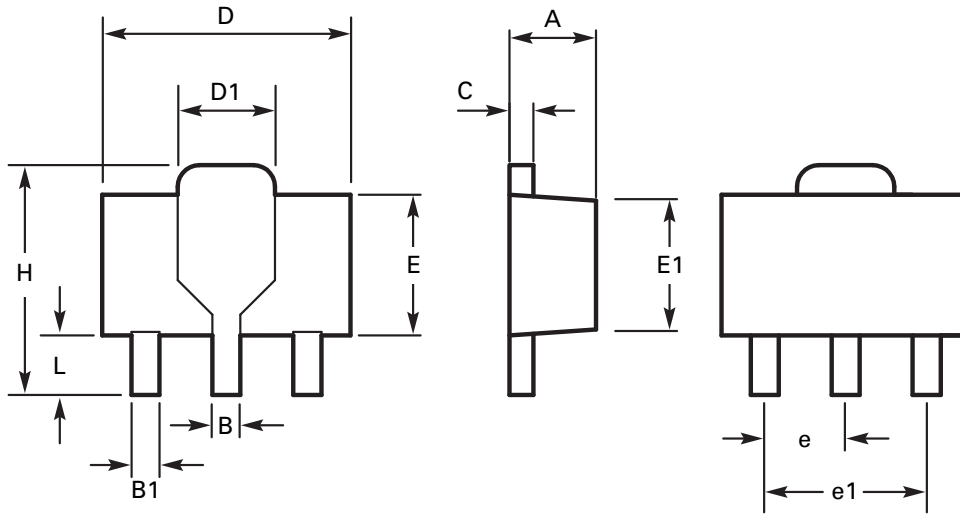
(\*) Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

### Typical characteristics



# ZXTP19020DZ

## Package outline - SOT89



DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	1.40	1.60	0.550	0.630	E	2.29	2.60	0.090	0.102
B	0.44	0.56	0.017	0.022	E1	2.13	2.29	0.084	0.090
B1	0.36	0.48	0.014	0.019	e	1.50 BSC		0.059 BSC	
C	0.35	0.44	0.014	0.017	e1	3.00 BSC		0.118 BSC	
D	4.40	4.60	0.173	0.181	H	3.94	4.25	0.155	0.167
D1	1.52	1.83	0.064	0.072	L	0.89	1.20	0.035	0.047

**Note:** Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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